

### 1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors



**Product data sheet** 

# 1. General description

Planar passivated high commutation three quadrant triac in a SOT78D (TO-220AB) internally insulated plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series C" triac will commutate the full RMS current at the maximum rated junction temperature without the aid of a snubber. This device has an internally isolated mounting base.

#### 2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- Isolated mounting base with 2500 V (RMS) isolation
- Less sensitive gate for high noise immunity
- Planar passivated for voltage ruggedness and reliability
- · Triggering in three quadrants only

## 3. Applications

- Electronic thermostats (heating and cooling)
- Motor controls
- · Rectifier-fed DC inductive loads e.g. DC motors and solenoids

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage			-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5		-	-	100	Α
T <sub>j</sub>	junction temperature			-	-	125	°C
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 84 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 3		-	-	12	Α
Static characte	eristics		,				
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		2	-	35	mA





**3Q Hi-Com Triac** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	2	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	2	-	35	mA

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2		Sym051
3	G	gate		·
mb	n.c.	mounting base; isolated		
			TO-220AB (SOT78D)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BTA312Y-600C	TO-220AB	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220	SOT78D		

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 84 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	12	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 20  \text{ms}$ ; Fig. 4; Fig. 5	-	100	Α
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 16.7  \text{ms}$	-	110	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	50	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	125	°C
T <sub>j</sub>	junction temperature		-	125	°C

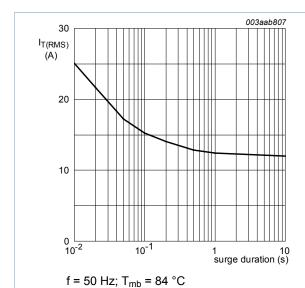


Fig. 1. RMS on-state current as a function of surge duration; maximum values

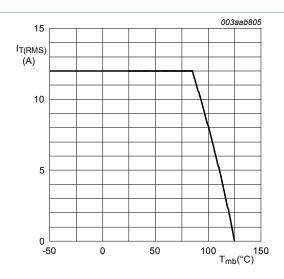
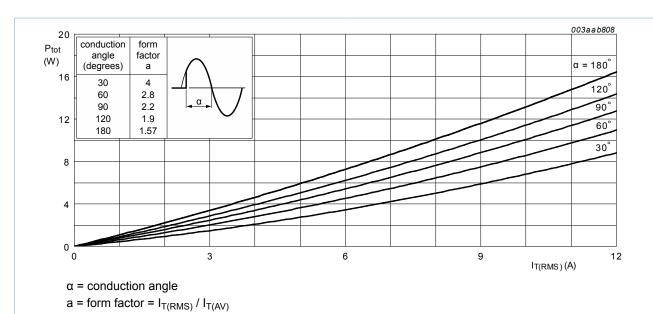
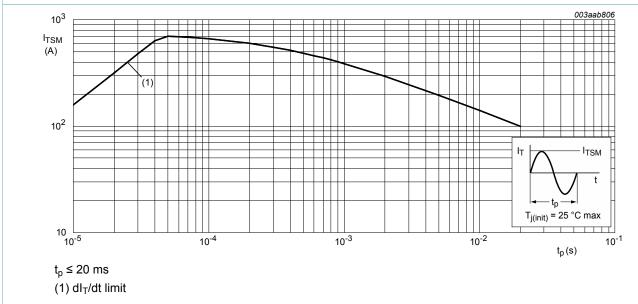


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

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Total power dissipation as a function of RMS on-state current; maximum values Fig. 3.



Non-repetitive peak on-state current as a function of pulse duration; maximum values Fig. 4.

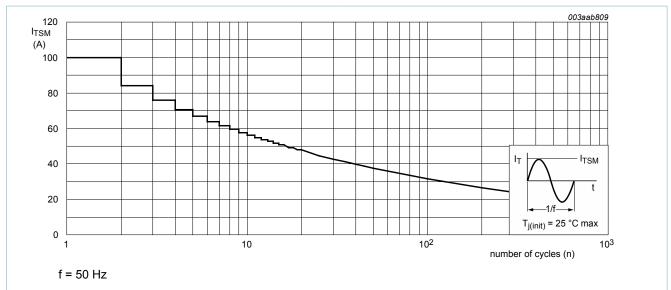


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

**3Q Hi-Com Triac** 

### 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	2.3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

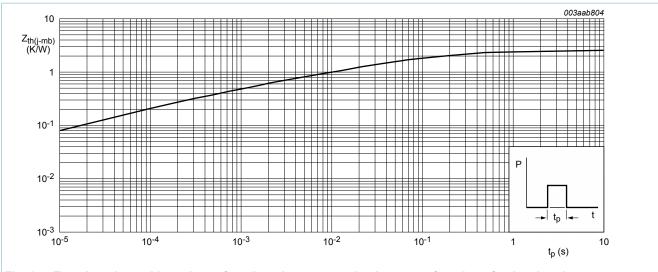


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

#### 9. Isolation characteristics

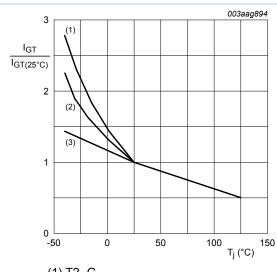
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; $T_{mb}$ = 25 °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>mb</sub> = 25 °C	-	10	-	pF

## 10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		,			
I <sub>GT</sub> gate trigger current	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	2	-	35	mA
	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	2	-	35	mA	
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	2	-	35	mA
I <sub>L</sub> latching current	latching current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 8}}$	-	-	50	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	50	mA
Ін	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	35	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
V <sub>GT</sub> gat	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.8	1	V
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic cl	naracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	500	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 12 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; (snubberless condition); gate open circuit	20	-	-	A/ms
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 20 A; $V_D$ = 600 V; $I_G$ = 0.1 A; $dI_G/$ dt = 5 A/µs	-	2	-	μs



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

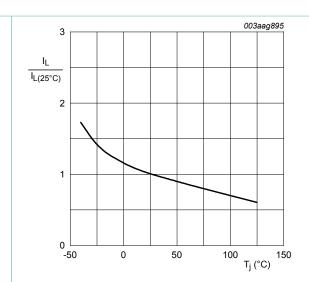


Fig. 8. Normalized latching current as a function of junction temperature

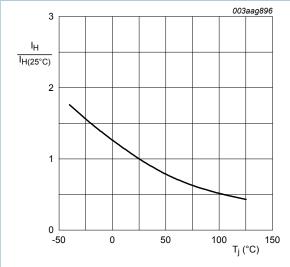
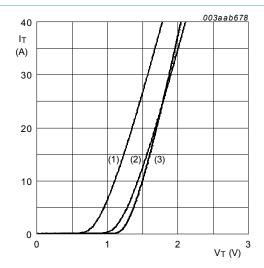


Fig. 9. Normalized holding current as a function of junction temperature



- $V_o$  = 1.164 V;  $R_s$  = 0.027  $\Omega$
- (1) T<sub>j</sub> = 125 °C; typical values
- (2) T<sub>i</sub> = 125 °C; maximum values
- (3) T<sub>i</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

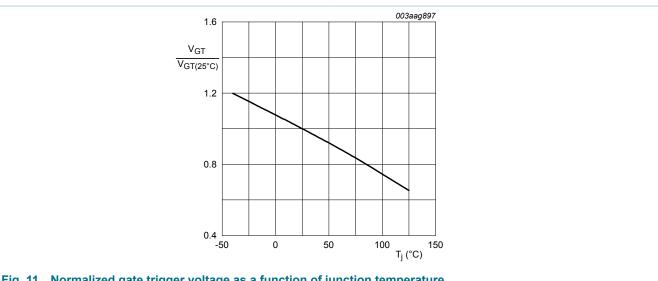
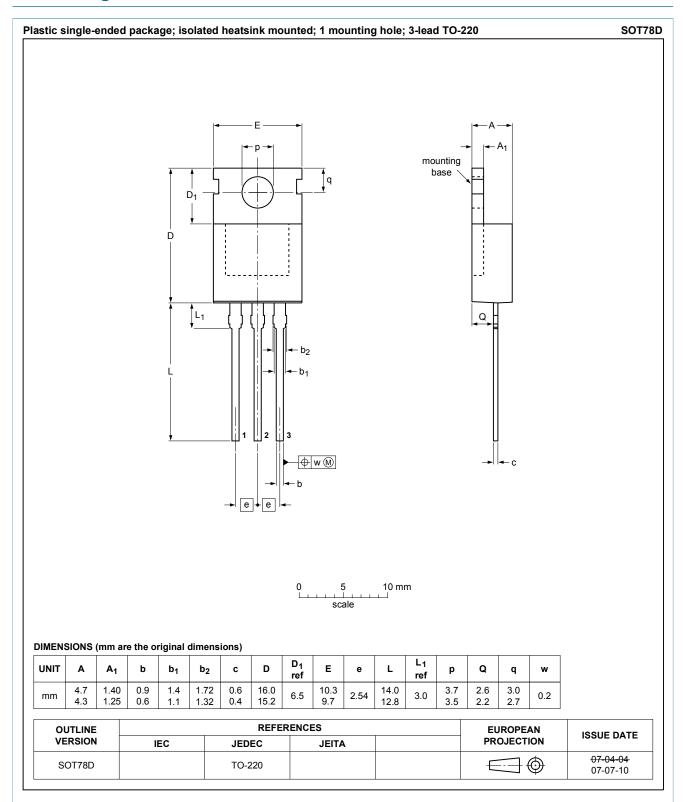


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

# 11. Package outline



**Product data sheet** 

### 12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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**3Q Hi-Com Triac** 

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